TENTATIVE TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

# 524,288-WORD BY 16-BIT FULL CMOS STATIC RAM

## DESCRIPTION

The TC55W800XB is a 8,388,608-bit static random access memory (SRAM) organized as 524,288 words by 16 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 2.3 to 3.3 V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 3 mA/MHz and a minimum cycle time of 70 ns. It is automatically placed in low-power mode at 0.5 μA standby current (at $V_{DD}$ = 3 V, Ta = 25°C, maximum) when chip enable ($\overline{CE1}$) is asserted high or (CE2) is asserted low. There are three control inputs. $\overline{CE1}$ and CE2 are used to select the device and for data retention control, and output enable ($\overline{OE}$) provides fast memory access. Data byte control pin ($\overline{LB}$, $\overline{UB}$) provides lower and upper byte access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. And, with a guaranteed operating extreme temperature range of −40° to 85°C, the TC55W800XB can be used in environments exhibiting extreme temperature conditions. The TC55W800XB is available in a plastic 48-ball BGA.

## FEATURES

- Low-power dissipation
  Operating: 9.9 mW/MHz (typical)
- Single power supply voltage of 2.3 to 3.3 V
- Power down features using $\overline{CE1}$ and CE2
- Data retention supply voltage of 1.5 to 3.3 V
- Direct TTL compatibility for all inputs and outputs
- Wide operating temperature range of −40° to 85°C
- Standby Current (maximum):

| | |
|---|---|
| 3.3 V | 10 μA |
| 3.0 V | 5 μA |

- Access Times (maximum at $V_{DD}$ = 2.7 to 3.3 V):

| | TC55W800XB | |
|---|---|---|
| | 7 | 8 |
| Access Time | 70 ns | 85 ns |
| $\overline{CE1}$ Access Time | 70 ns | 85 ns |
| CE2 Access Time | 70 ns | 85 ns |
| $\overline{OE}$ Access Time | 35 ns | 45 ns |

- Package:
  P-TFBGA48-0811-0.75AZ (Weight: 0.21 g typ)

## PIN ASSIGNMENT (TOP VIEW)

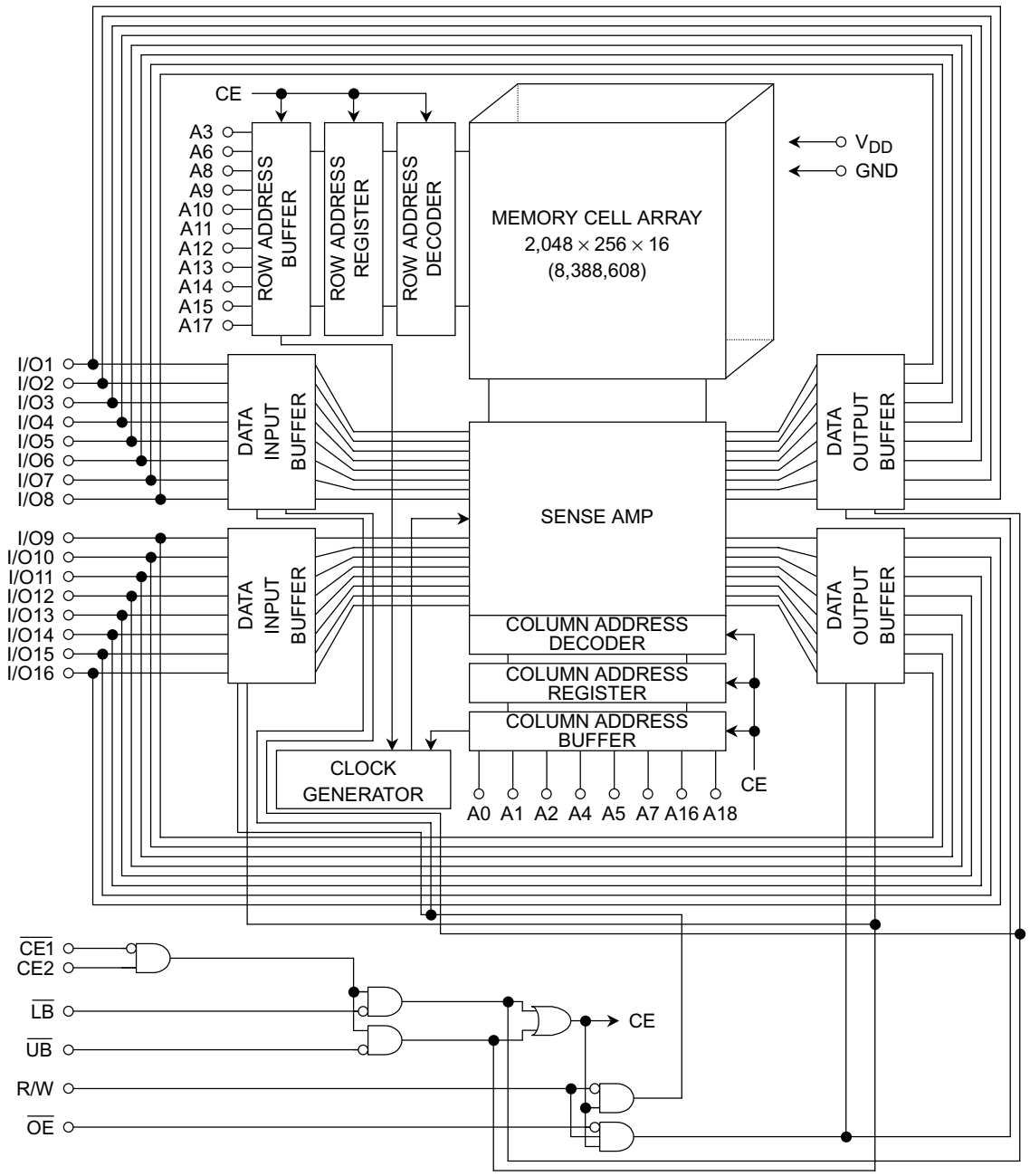
48 PIN BGA

| | 1 | 2 | 3 | 4 | 5 | 6 |
|---|---|---|---|---|---|---|
| A | $\overline{LB}$ | $\overline{OE}$ | A0 | A1 | A2 | CE2 |
| B | I/O9 | $\overline{UB}$ | A3 | A4 | $\overline{CE1}$ | I/O1 |
| C | I/O10 | I/O11 | A5 | A6 | I/O2 | I/O3 |
| D | $V_{SS}$ | I/O12 | A17 | A7 | I/O4 | $V_{DD}$ |
| E | $V_{DD}$ | I/O13 | NC | A16 | I/O5 | $V_{SS}$ |
| F | I/O15 | I/O14 | A14 | A15 | I/O6 | I/O7 |
| G | I/O16 | NC | A12 | A13 | R/W | I/O8 |
| H | A18 | A8 | A9 | A10 | A11 | NC |

## PIN NAMES

| | |
|---|---|
| A0~A18 | Address Inputs |
| $\overline{CE1}$, CE2 | Chip Enable |
| R/W | Read/Write Control |
| $\overline{OE}$ | Output Enable |
| $\overline{LB}$, $\overline{UB}$ | Data Byte Control |
| I/O1~I/O16 | Data Inputs/Outputs |
| $V_{DD}$ | Power |
| GND | Ground |
| NC | No Connection |

## BLOCK DIAGRAM




## OPERATING MODE

| MODE | $\overline{CE1}$ | CE2 | $\overline{OE}$ | R/W | $\overline{LB}$ | $\overline{UB}$ | I/O1~I/O8 | I/O9~I/O16 | POWER |
|---|---|---|---|---|---|---|---|---|---|
| Read | L | H | L | H | L | L | Output | Output | $I_{DDO}$ |
| | L | H | L | H | H | L | High-Z | Output | $I_{DDO}$ |
| | L | H | L | H | L | H | Output | High-Z | $I_{DDO}$ |
| Write | L | H | * | L | L | L | Input | Input | $I_{DDO}$ |
| | L | H | * | L | H | L | High-Z | Input | $I_{DDO}$ |
| | L | H | * | L | L | H | Input | High-Z | $I_{DDO}$ |
| Output Deselect | L | H | H | H | * | * | High-Z | High-Z | $I_{DDO}$ |
| Standby | H | * | * | * | * | * | High-Z | High-Z | $I_{DDS}$ |
| | * | L | * | * | * | * | High-Z | High-Z | $I_{DDS}$ |
| | * | * | * | * | H | H | High-Z | High-Z | $I_{DDS}$ |

* = don't care
H = logic high
L = logic low

## MAXIMUM RATINGS

| SYMBOL | RATING | VALUE | UNIT |
|---|---|---|---|
| $V_{DD}$ | Power Supply Voltage | −0.3~4.2 | V |
| $V_{IN}$ | Input Voltage | −0.3*~4.2 | V |
| $V_{I/O}$ | Input/Output Voltage | −0.5~$V_{DD}$ + 0.5 | V |
| $P_D$ | Power Dissipation | 0.6 | W |
| $T_{solder}$ | Soldering Temperature (10s) | 260 | °C |
| $T_{stg}$ | Storage Temperature | −55~125 | °C |
| $T_{opr}$ | Operating Temperature | −40~85 | °C |

*: −2.0 V when measured at a pulse width of 25ns

## DC RECOMMENDED OPERATING CONDITIONS (Ta = −40° to 85°C)

| SYMBOL | PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{DD}$ | Power Supply Voltage | | 2.3 | — | 3.3 | V |
| $V_{IH}$ | Input High Voltage | $V_{DD}$ = 2.3 V~3.3 V | 2.0 | — | $V_{DD}$ + 0.3 | V |
| | | $V_{DD}$ = 2.7 V~3.3 V | 2.2 | | | |
| $V_{IL}$ | Input Low Voltage | | −0.3* | — | $V_{DD}$ × 0.22 | V |
| $V_{DH}$ | Data Retention Supply Voltage | | 1.5 | — | 3.3 | V |

*: −2.0 V when measured at a pulse width of 25ns

## DC CHARACTERISTICS (Ta = –40° to 85°C, $V_{DD}$ = 2.3 to 3.3 V)

| SYMBOL | PARAMETER | TEST CONDITION | | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|---|
| $I_{IL}$ | Input Leakage Current | $V_{IN}$ = 0 V~$V_{DD}$ | | | | — | — | ±1.0 | μA |
| $I_{OH}$ | Output High Current | $V_{OH}$ = $V_{DD}$ – 0.5 V | | | | –0.5 | — | — | mA |
| $I_{OL}$ | Output Low Current | $V_{OL}$ = 0.4 V | | | | 2.1 | — | — | mA |
| $I_{LO}$ | Output Leakage Current | $\overline{CE1}$ = $V_{IH}$ or CE2 = $V_{IL}$ or $\overline{LB}$ and $\overline{UB}$ = $V_{IH}$ or R/W = $V_{IL}$ or $\overline{OE}$ = $V_{IH}$, $V_{OUT}$ = 0 V~$V_{DD}$ | | | | — | — | ±1.0 | μA |
| $I_{DDO1}$ | Operating Current | $\overline{CE1}$ = $V_{IL}$ and CE2 = $V_{IH}$ and $\overline{LB}$ and $\overline{UB}$ = $V_{IL}$ and R/W = $V_{IH}$ and $I_{OUT}$ = 0 mA and Other Input = $V_{IH}$/$V_{IL}$ | | $t_{cycle}$ | min | — | — | 50 | mA |
| | | | | | 1 μs | — | — | 10 | |
| $I_{DDO2}$ | | $\overline{CE1}$ = 0.2 V and CE2 = $V_{DD}$ – 0.2 V and $\overline{LB}$ and $\overline{UB}$ = 0.2 V, R/W = $V_{DD}$ – 0.2 V and $I_{OUT}$ = 0 mA, Other Input = $V_{DD}$ – 0.2 V/0.2 V | | $t_{cycle}$ | min | — | — | 45 | mA |
| | | | | | 1 μs | — | — | 5 | |
| $I_{DDS1}$ | Standby Current | $\overline{CE1}$ = $V_{IH}$ or CE2 = $V_{IL}$ or $\overline{LB}$ and $\overline{UB}$ = $V_{IH}$ | | | | — | — | 2 | mA |
| $I_{DDS2}$ (Note) | | $\overline{CE1}$ = $V_{DD}$ – 0.2 V or CE2 = 0.2 V or $\overline{LB}$ and $\overline{UB}$ = $V_{DD}$ – 0.2 V, $V_{DD}$ = 1.5 V~3.3 V | $V_{DD}$ = 3.0 V ± 10% | Ta = 25°C | | — | — | 1 | μA |
| | | | | Ta = –40~85°C | | — | — | 10 | |
| | | | $V_{DD}$ = 3.0 V | Ta = 25°C | | — | 0.05 | 0.5 | |
| | | | | Ta = –40~40°C | | — | — | 1 | |
| | | | | Ta = –40~85°C | | — | — | 5 | |

Note • In standby mode with $\overline{CE1}$ ≥ $V_{DD}$ – 0.2 V, these limits are assured for the condition CE2 ≥ $V_{DD}$ – 0.2 V or CE2 ≤ 0.2 V.

• In standby mode with $\overline{LB}$ and $\overline{UB}$ ≥ $V_{DD}$ – 0.2 V, these limits are assured for the condition $\overline{CE1}$ ≥ $V_{DD}$ – 0.2 V or $\overline{CE1}$ ≤ 0.2 V and CE2 ≥ $V_{DD}$ – 0.2 V or CE2 ≤ 0.2 V.

## CAPACITANCE (Ta = 25°C, f = 1 MHz)

| SYMBOL | PARAMETER | TEST CONDITION | MAX | UNIT |
|---|---|---|---|---|
| $C_{IN}$ | Input Capacitance | $V_{IN}$ = GND | 10 | pF |
| $C_{OUT}$ | Output Capacitance | $V_{OUT}$ = GND | 10 | pF |

Note: This parameter is periodically sampled and is not 100% tested.

## AC CHARACTERISTICS AND OPERATING CONDITIONS

**(Ta = –40° to 85°C, $V_{DD}$ = 2.7 to 3.3 V)**

READ CYCLE

| SYMBOL | PARAMETER | TC55W800XB | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 7 | | 8 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{RC}$ | Read Cycle Time | 70 | — | 85 | — | ns |
| $t_{ACC}$ | Address Access Time | — | 70 | — | 85 | |
| $t_{CO1}$ | Chip Enable( $\overline{CE1}$ ) Access Time | — | 70 | — | 85 | |
| $t_{CO2}$ | Chip Enable(CE2) Access Time | — | 70 | — | 85 | |
| $t_{OE}$ | Output Enable Access Time | — | 35 | — | 45 | |
| $t_{BA}$ | Data Byte Control Access Time | — | 70 | — | 85 | |
| $t_{COE}$ | Chip Enable Low to Output Active | 5 | — | 5 | — | |
| $t_{OEE}$ | Output Enable Low to Output Active | 0 | — | 0 | — | |
| $t_{BE}$ | Data Byte Control Low to Output Active | 0 | — | 0 | — | |
| $t_{OD}$ | Chip Enable High to Output High-Z | — | 30 | — | 35 | |
| $t_{ODO}$ | Output Enable High to Output High-Z | — | 30 | — | 35 | |
| $t_{BD}$ | Data Byte Control High to Output High-Z | — | 30 | — | 35 | |
| $t_{OH}$ | Output Data Hold Time | 10 | — | 10 | — | |

WRITE CYCLE

| SYMBOL | PARAMETER | TC55W800XB | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 7 | | 8 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{WC}$ | Write Cycle Time | 70 | — | 85 | — | ns |
| $t_{WP}$ | Write Pulse Width | 50 | — | 55 | — | |
| $t_{CW}$ | Chip Enable to End of Write | 60 | — | 70 | — | |
| $t_{BW}$ | Data Byte Control to End of Write | 60 | — | 70 | — | |
| $t_{AS}$ | Address Setup Time | 0 | — | 0 | — | |
| $t_{WR}$ | Write Recovery Time | 0 | — | 0 | — | |
| $t_{ODW}$ | R/W Low to Output High-Z | — | 30 | — | 35 | |
| $t_{OEW}$ | R/W High to Output Active | 0 | — | 0 | — | |
| $t_{DS}$ | Data Setup Time | 30 | — | 35 | — | |
| $t_{DH}$ | Data Hold Time | 0 | — | 0 | — | |

## AC TEST CONDITIONS

| PARAMETER | TEST CONDITION |
|---|---|
| Output load | 30 pF + 1 TTL Gate |
| Input pulse level | 0.4 V, 2.4 V |
| Timing measurements | $V_{DD} \times 0.5$ |
| Reference level | $V_{DD} \times 0.5$ |
| $t_R$, $t_F$ | 5 ns |

## AC CHARACTERISTICS AND OPERATING CONDITIONS

**(Ta = –40° to 85°C, $V_{DD}$ = 2.3 to 3.3 V)**

READ CYCLE

| SYMBOL | PARAMETER | TC55W800XB | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 7 | | 8 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{RC}$ | Read Cycle Time | 85 | — | 100 | — | ns |
| $t_{ACC}$ | Address Access Time | — | 85 | — | 100 | |
| $t_{CO1}$ | Chip Enable( $\overline{CE1}$ ) Access Time | — | 85 | — | 100 | |
| $t_{CO2}$ | Chip Enable(CE2) Access Time | — | 85 | — | 100 | |
| $t_{OE}$ | Output Enable Access Time | — | 45 | — | 50 | |
| $t_{BA}$ | Data Byte Control Access Time | — | 85 | — | 100 | |
| $t_{COE}$ | Chip Enable Low to Output Active | 5 | — | 5 | — | |
| $t_{OEE}$ | Output Enable Low to Output Active | 0 | — | 0 | — | |
| $t_{BE}$ | Data Byte Control Low to Output Active | 0 | — | 0 | — | |
| $t_{OD}$ | Chip Enable High to Output High-Z | — | 35 | — | 40 | |
| $t_{ODO}$ | Output Enable High to Output High-Z | — | 35 | — | 40 | |
| $t_{BD}$ | Data Byte Control High to Output High-Z | — | 35 | — | 40 | |
| $t_{OH}$ | Output Data Hold Time | 10 | — | 10 | — | |

WRITE CYCLE

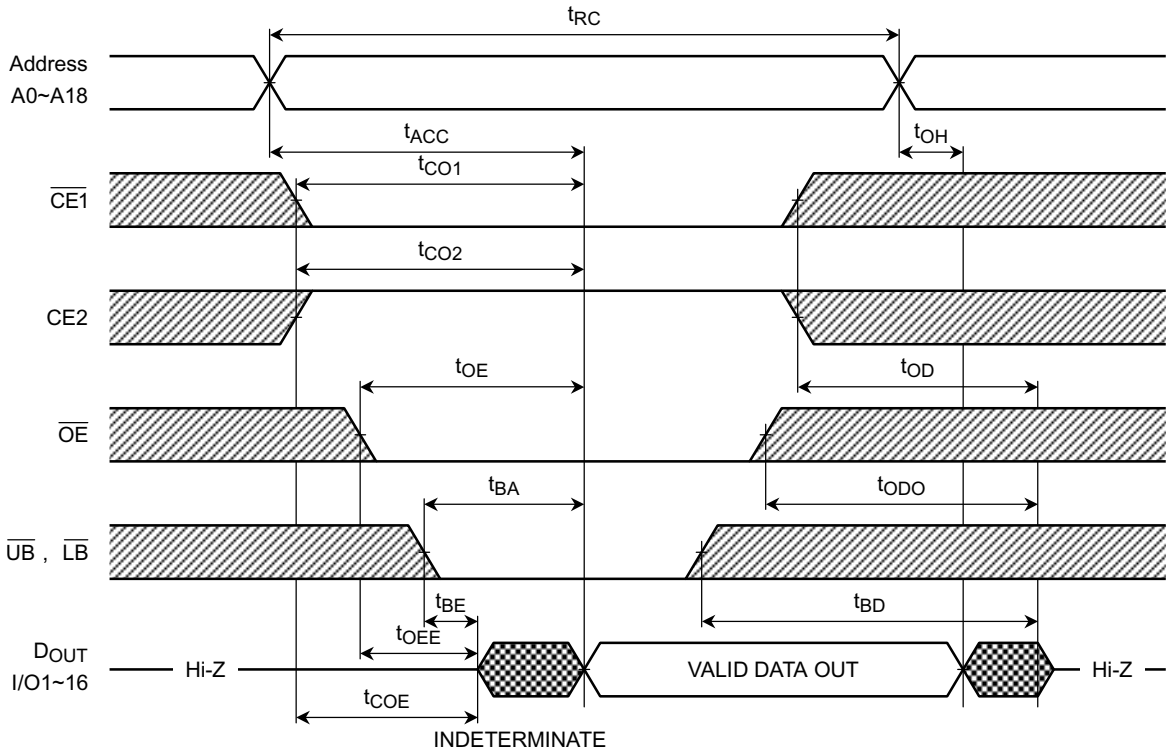
| SYMBOL | PARAMETER | TC55W800XB | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 7 | | 8 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{WC}$ | Write Cycle Time | 85 | — | 100 | — | ns |
| $t_{WP}$ | Write Pulse Width | 55 | — | 60 | — | |
| $t_{CW}$ | Chip Enable to End of Write | 70 | — | 80 | — | |
| $t_{BW}$ | Data Byte Control to End of Write | 70 | — | 80 | — | |
| $t_{AS}$ | Address Setup Time | 0 | — | 0 | — | |
| $t_{WR}$ | Write Recovery Time | 0 | — | 0 | — | |
| $t_{ODW}$ | R/W Low to Output High-Z | — | 35 | — | 40 | |
| $t_{OEW}$ | R/W High to Output Active | 0 | — | 0 | — | |
| $t_{DS}$ | Data Setup Time | 35 | — | 40 | — | |
| $t_{DH}$ | Data Hold Time | 0 | — | 0 | — | |

## AC TEST CONDITIONS

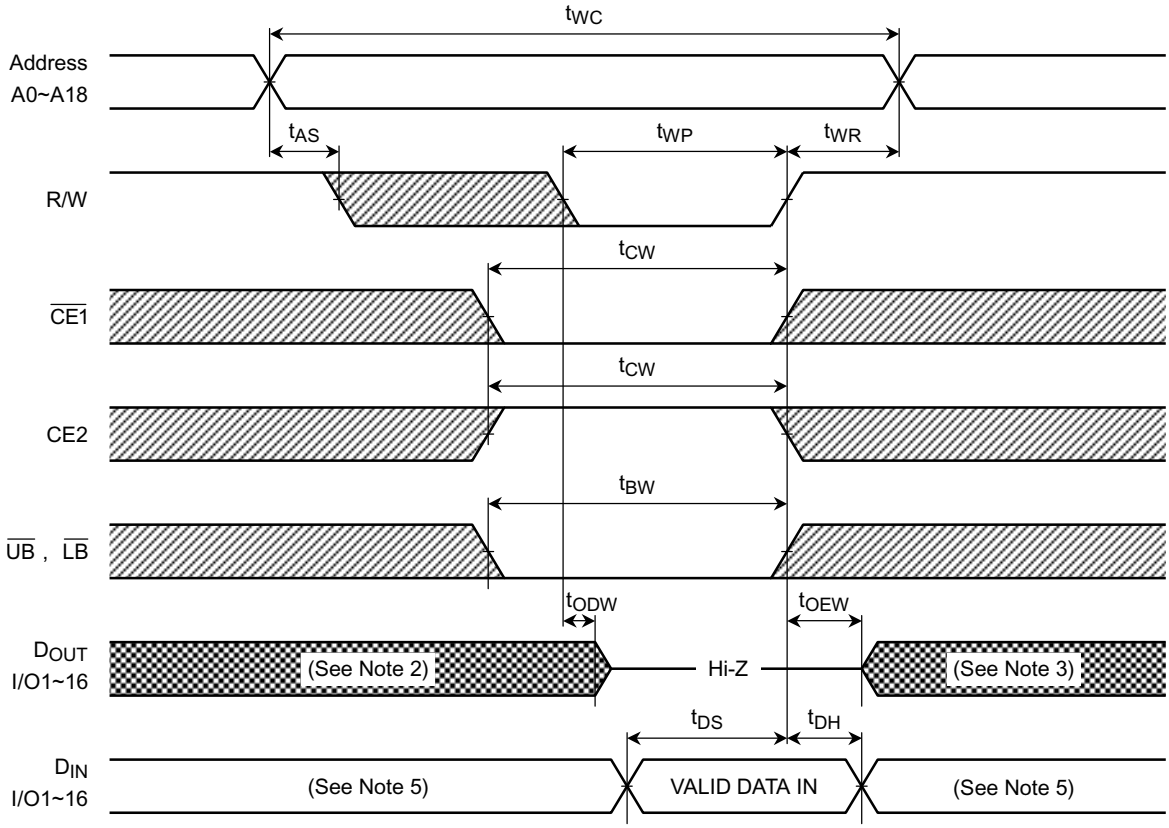
| PARAMETER | TEST CONDITION |
|---|---|
| Output load | 30 pF + 1 TTL Gate |
| Input pulse level | $V_{DD}$ – 0.2 V, 0.2 V |
| Timing measurements | $V_{DD} \times 0.5$ |
| Reference level | $V_{DD} \times 0.5$ |
| $t_R$, $t_F$ | 5 ns |

## TIMING DIAGRAMS

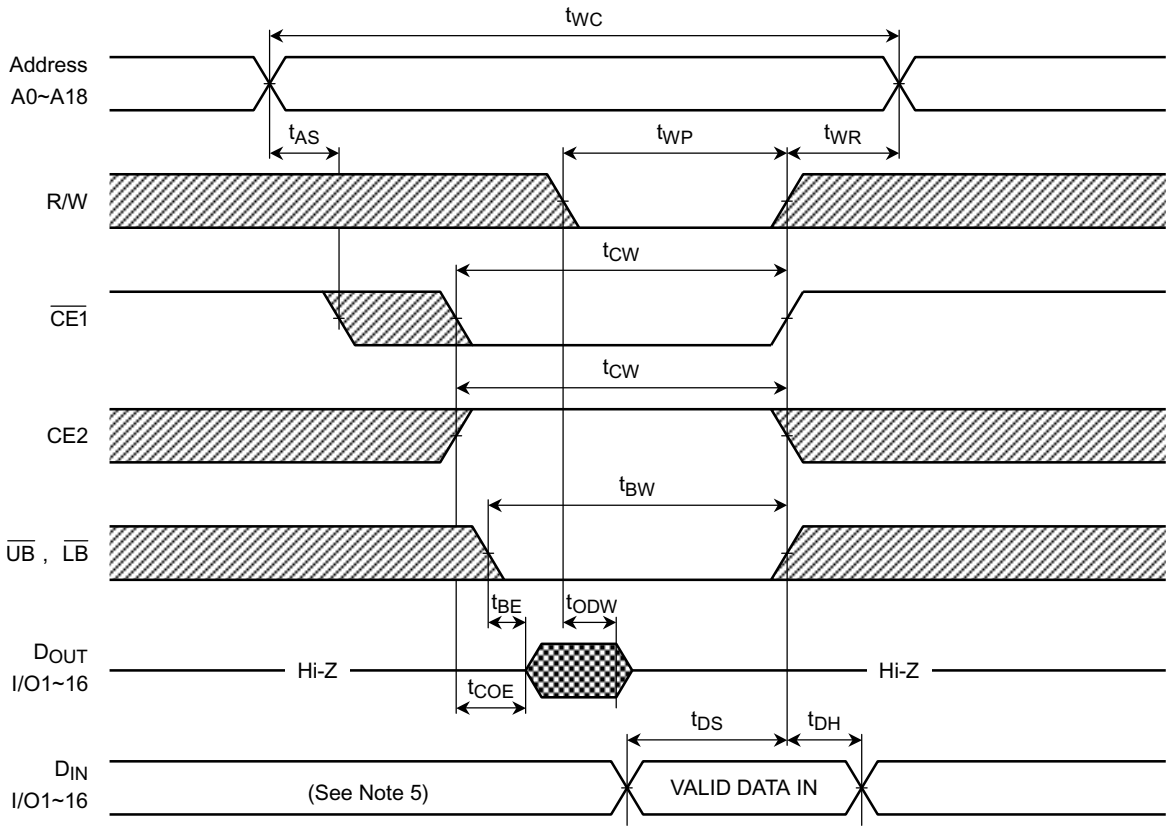
### READ CYCLE (See Note 1)



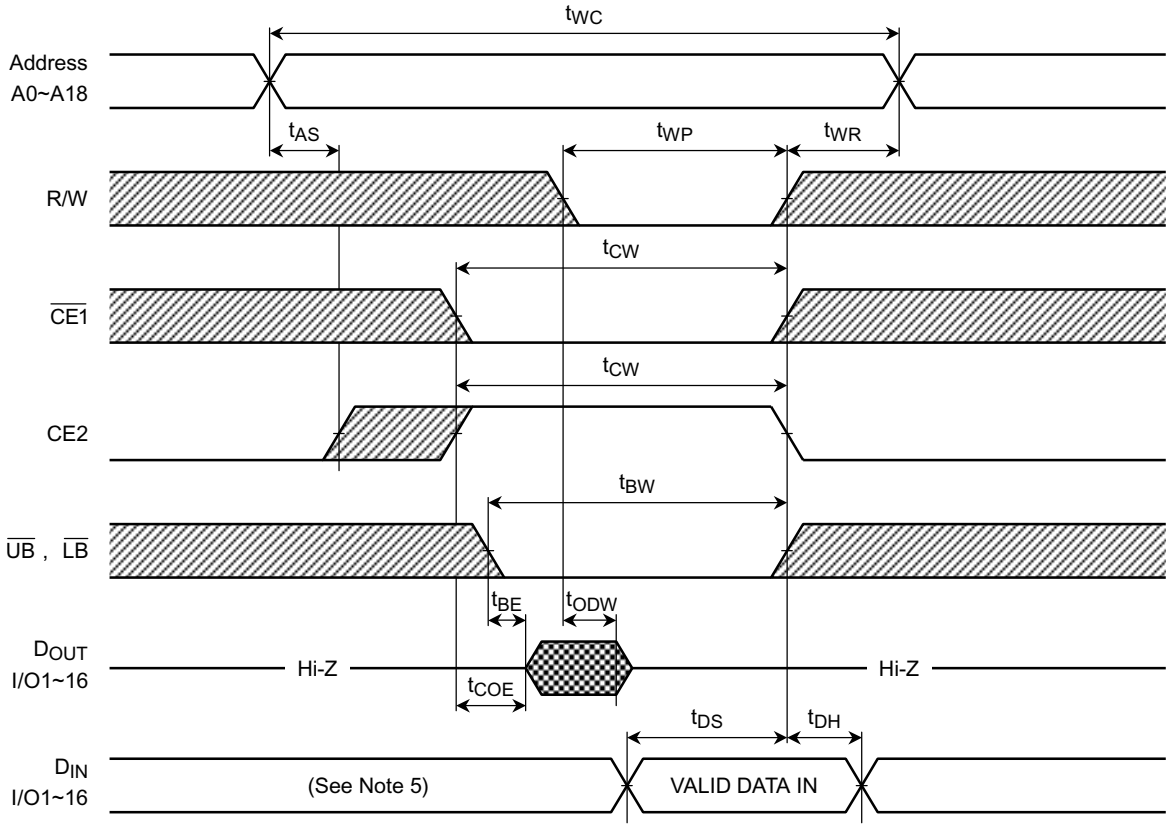

### WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



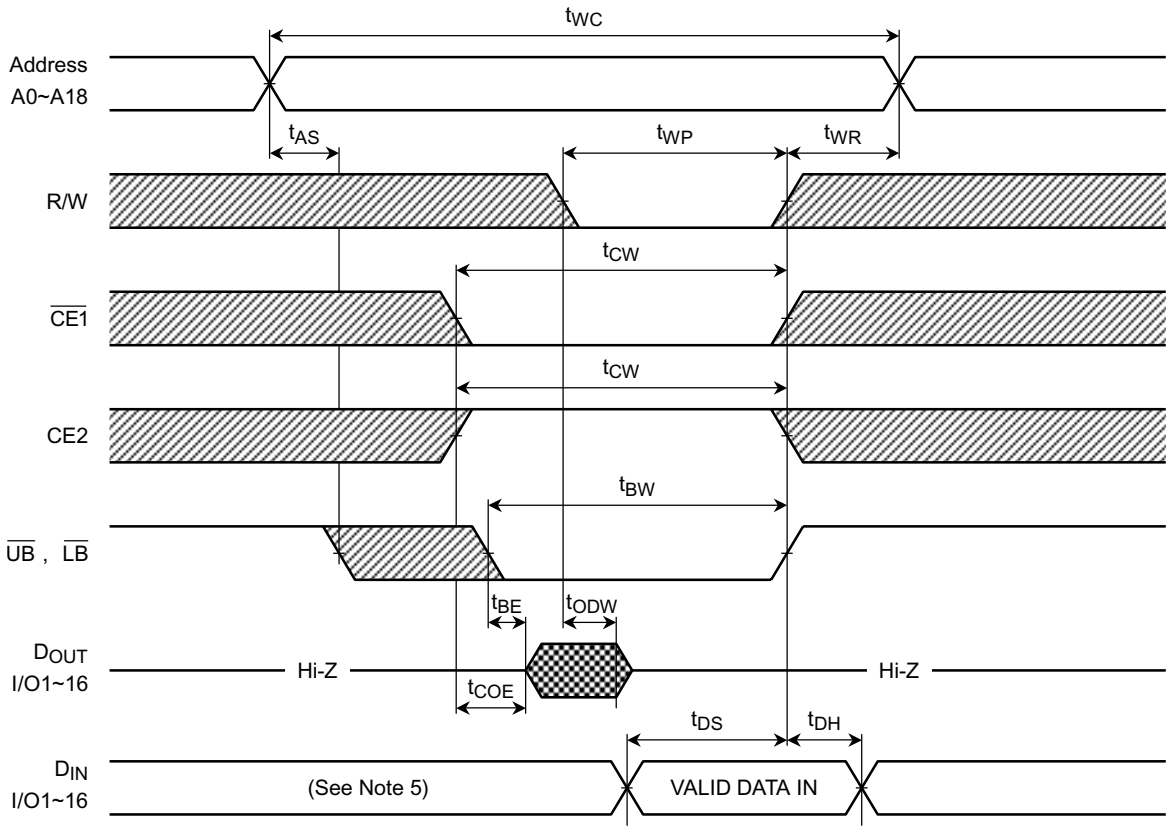
## WRITE CYCLE 2 ( $\overline{CE1}$ CONTROLLED) (See Note 4)




## WRITE CYCLE 3 (CE2 CONTROLLED) (See Note 4)



## WRITE CYCLE 4 ($\overline{UB}$, $\overline{LB}$ CONTROLLED) (See Note 4)




Note:

(1) R/W remains HIGH for the read cycle.

(2) If $\overline{CE1}$ goes LOW(or CE2 goes HIGH) coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If $\overline{CE1}$ goes HIGH(or CE2 goes LOW) coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

(4) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

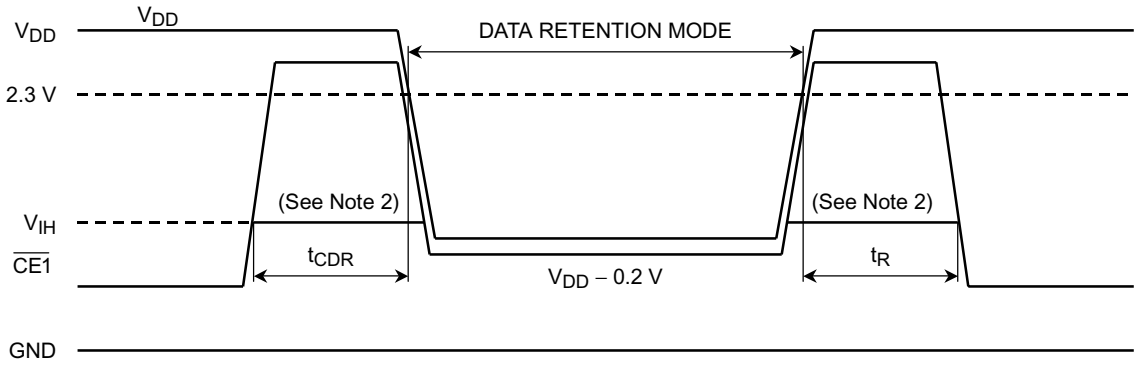
(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

## DATA RETENTION CHARACTERISTICS (Ta = –40° to 85°C)

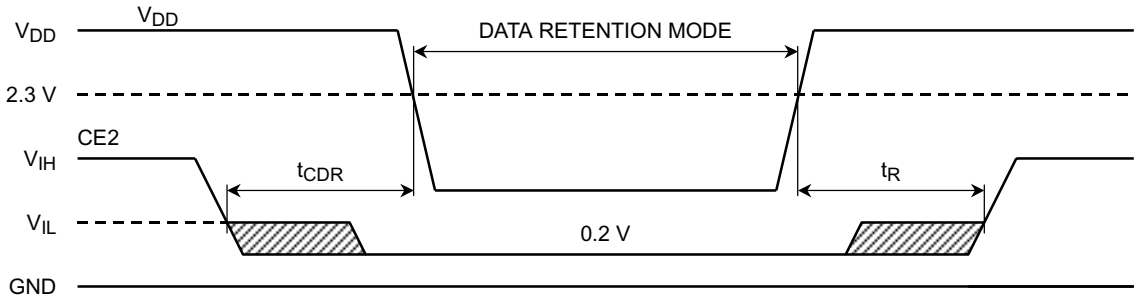
| SYMBOL | PARAMETER | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| $V_{DH}$ | Data Retention Supply Voltage | | | 1.5 | — | 3.3 | V |
| $I_{DDS2}$ | Standby Current | $V_{DH}$ = 3.3 V | Ta = –40~85°C | — | — | 10 | μA |
| | | $V_{DH}$ = 3.0 V | Ta = –40~40°C | — | — | 1 | |
| | | | Ta = –40~85°C | — | — | 5 | |
| $t_{CDR}$ | Chip Deselect to Data Retention Mode Time | | | 0 | — | — | ns |
| $t_R$ | Recovery Time | | | $t_{RC}$ (See Note) | — | — | ns |

Note: Read cycle time

### $\overline{CE1}$ CONTROLLED DATA RETENTION MODE (See Note 1)




### CE2 CONTROLLED DATA RETENTION MODE (See Note 3)




Note:

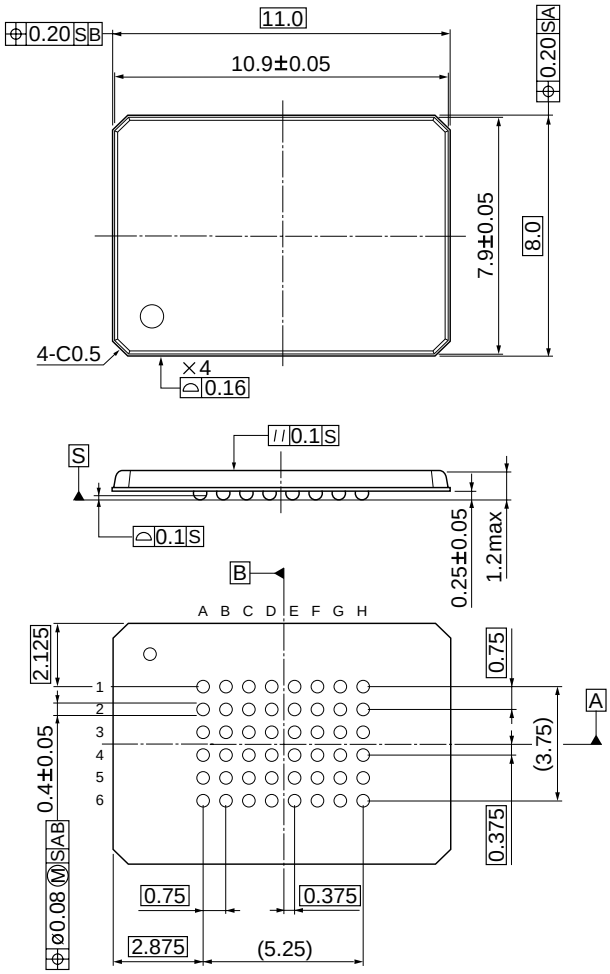
(1) In $\overline{CE1}$ controlled data retention mode, minimum standby current mode is entered when CE2 ≤ 0.2 V or CE2 ≥ $V_{DD}$ – 0.2 V.

(2) When $\overline{CE1}$ is operating at the $V_{IH}$ level, the operating current is given by $I_{DDS1}$ during the transition of $V_{DD}$ from 2.3 to 2.2V.

(3) In CE2 controlled data retention mode, minimum standby current mode is entered when CE2 ≤ 0.2 V.

## PACKAGE DIMENSIONS

P-TFBAG48-0811-0.75AZ Unit: mm




Weight: 0.21 g (typ)

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000707EBA

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